

Queen's Power Group

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A New Resonant Gate Drive Circuit with Center-Tapped Transformer

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Presentation Overview



- 1. Introduction***
- 2. Proposed Resonant Gate Drive Circuit**
- 3. Analysis and Design Guidelines**
- 4. Experimental Results**
- 5. Conclusions**

1. Introduction



- **Increased demand for higher switching frequencies:**
 - Size reduction
 - Fast loop response
- **BUT, Gate loss increases with frequency!**
- **Drawbacks of conventional gate drivers:**
 - **Gate charge completely lost**
 - Driver overheating
 - Slow RC discharge turn-off: **SWITCHING LOSS**

Presentation Overview



1. Introduction

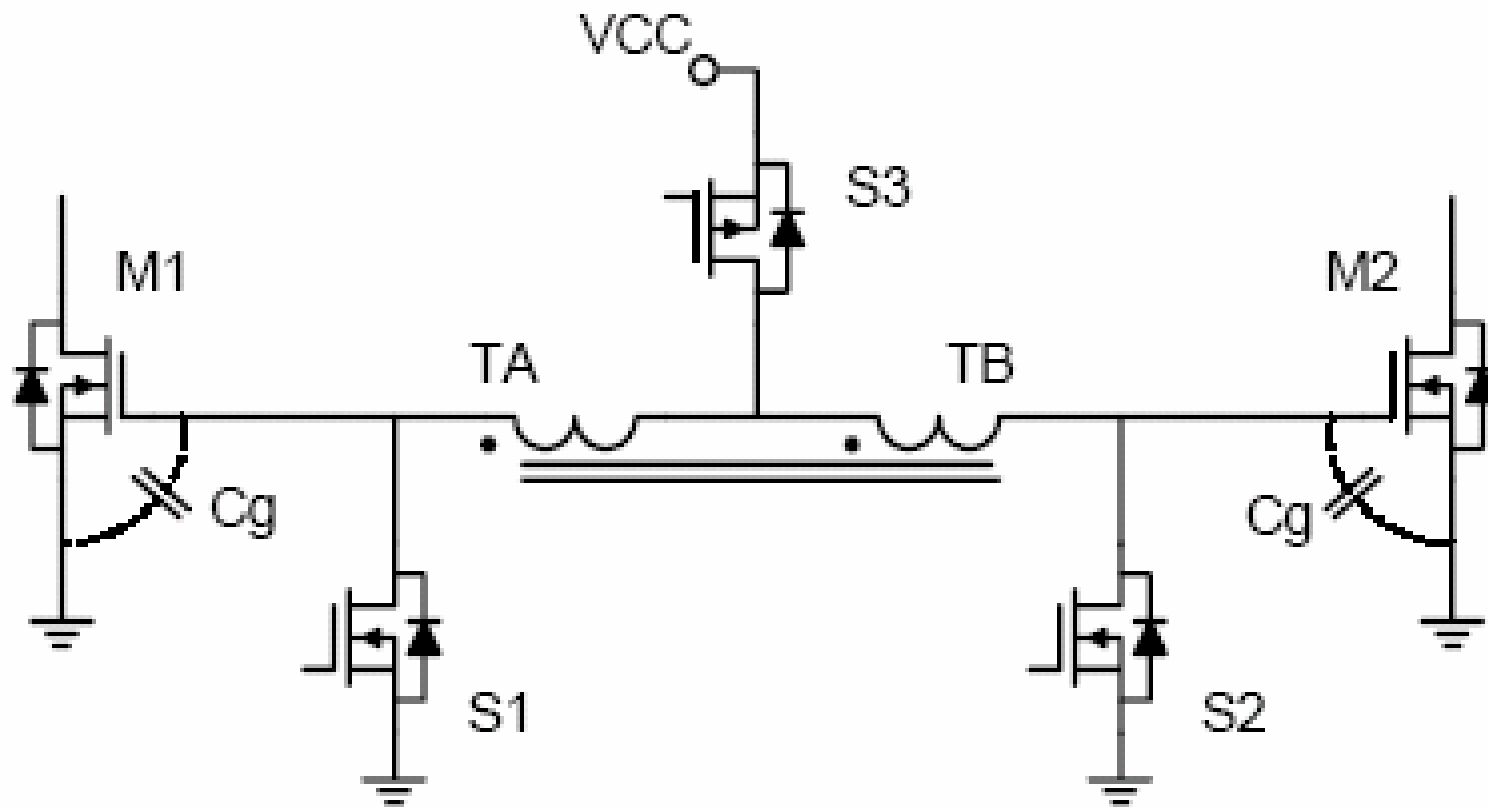
2. Proposed Resonant Gate Drive Circuit

3. Analysis and Design Guidelines

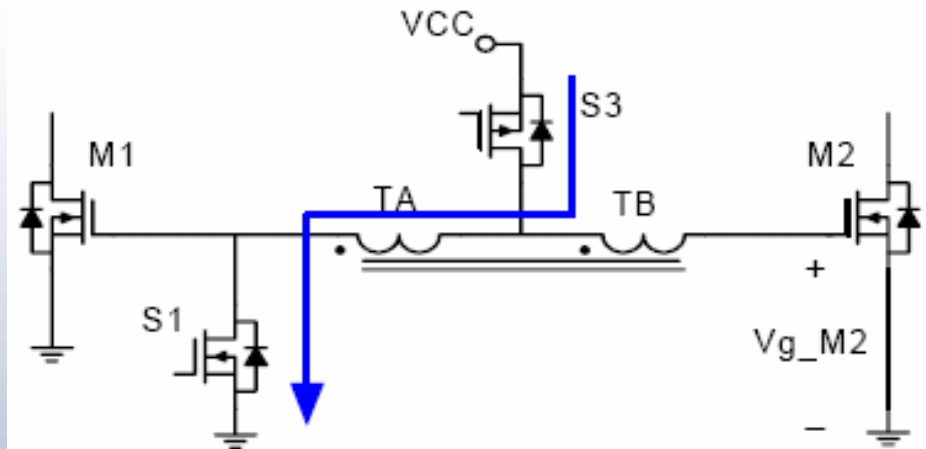
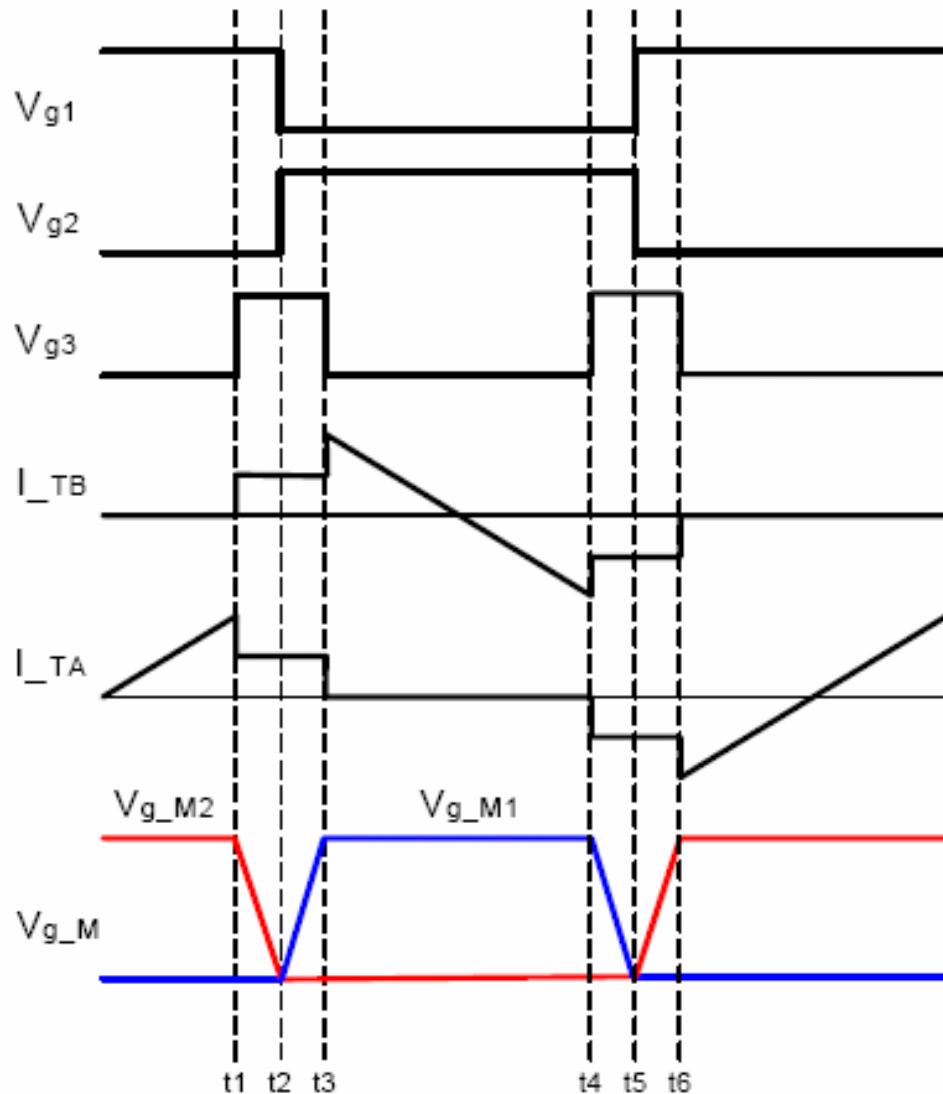
4. Experimental Results

5. Conclusions

2. Proposed Resonant Gate Drive Circuit



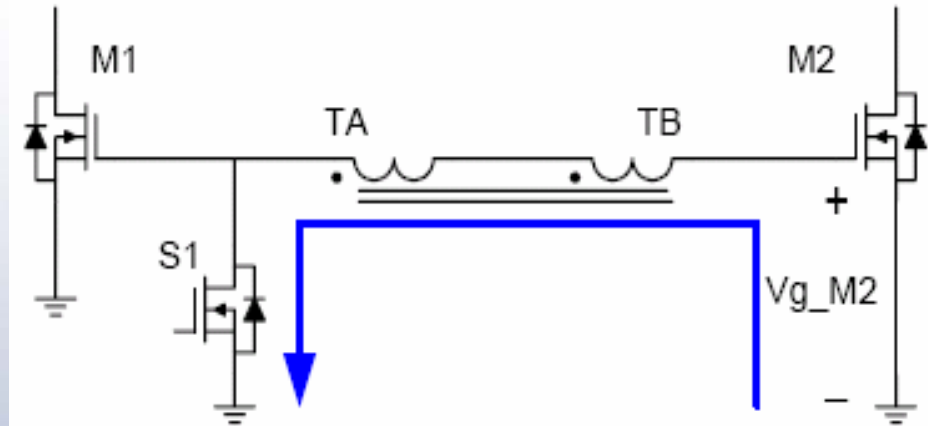
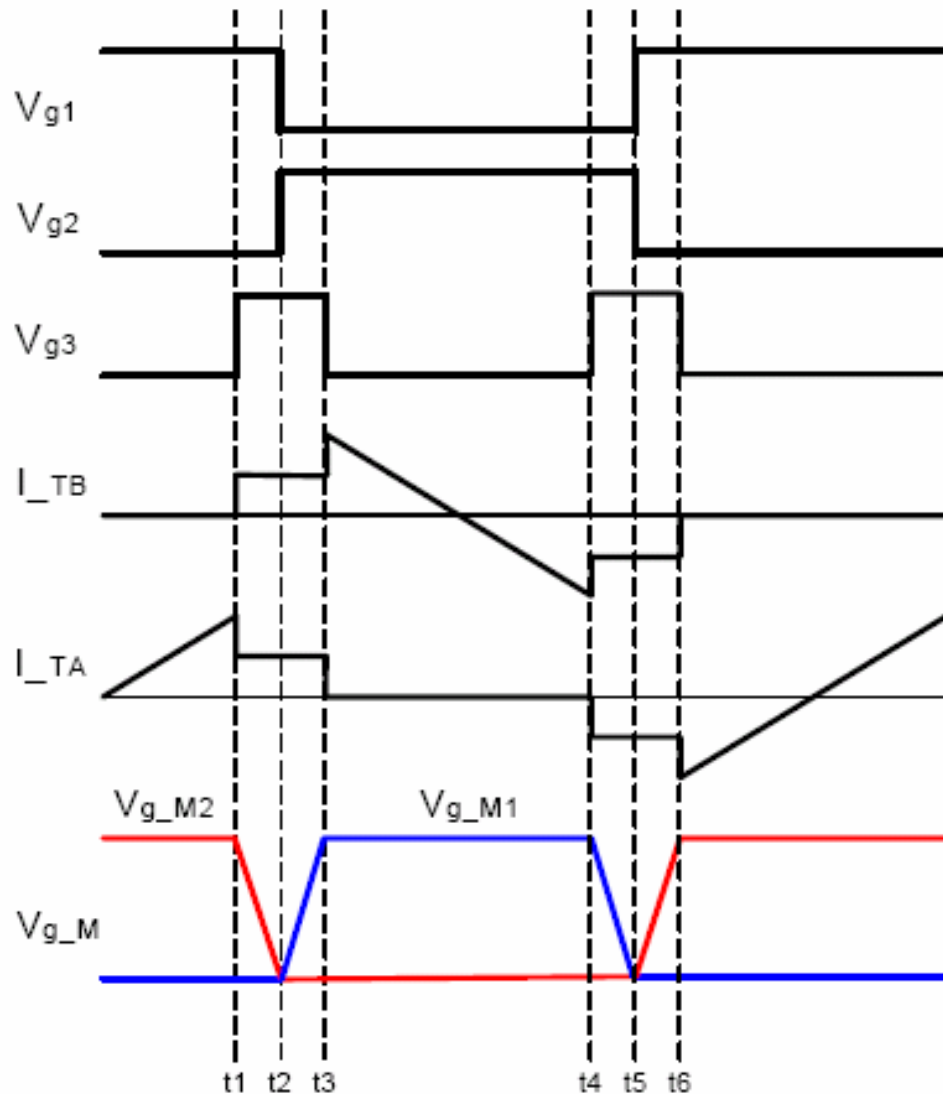
Operating Principles



Before t_1 :

1. $S1$ and $S3$ on
2. $M1$ off, $M2$ on
3. Gate voltage of $M2$ at twice of V_{cc}

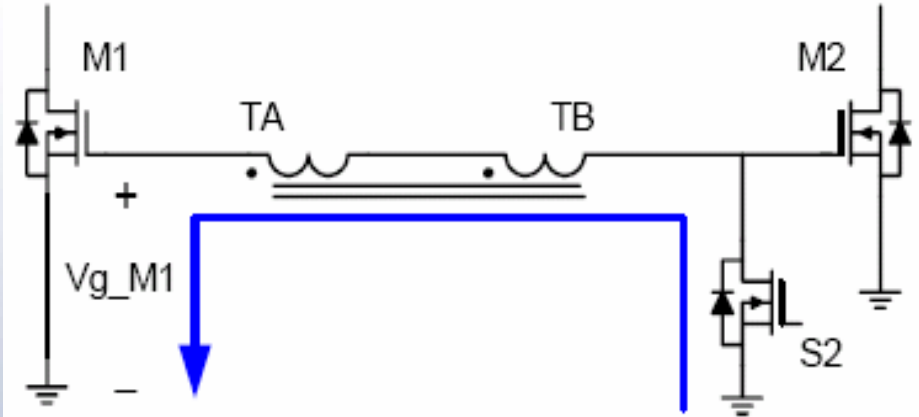
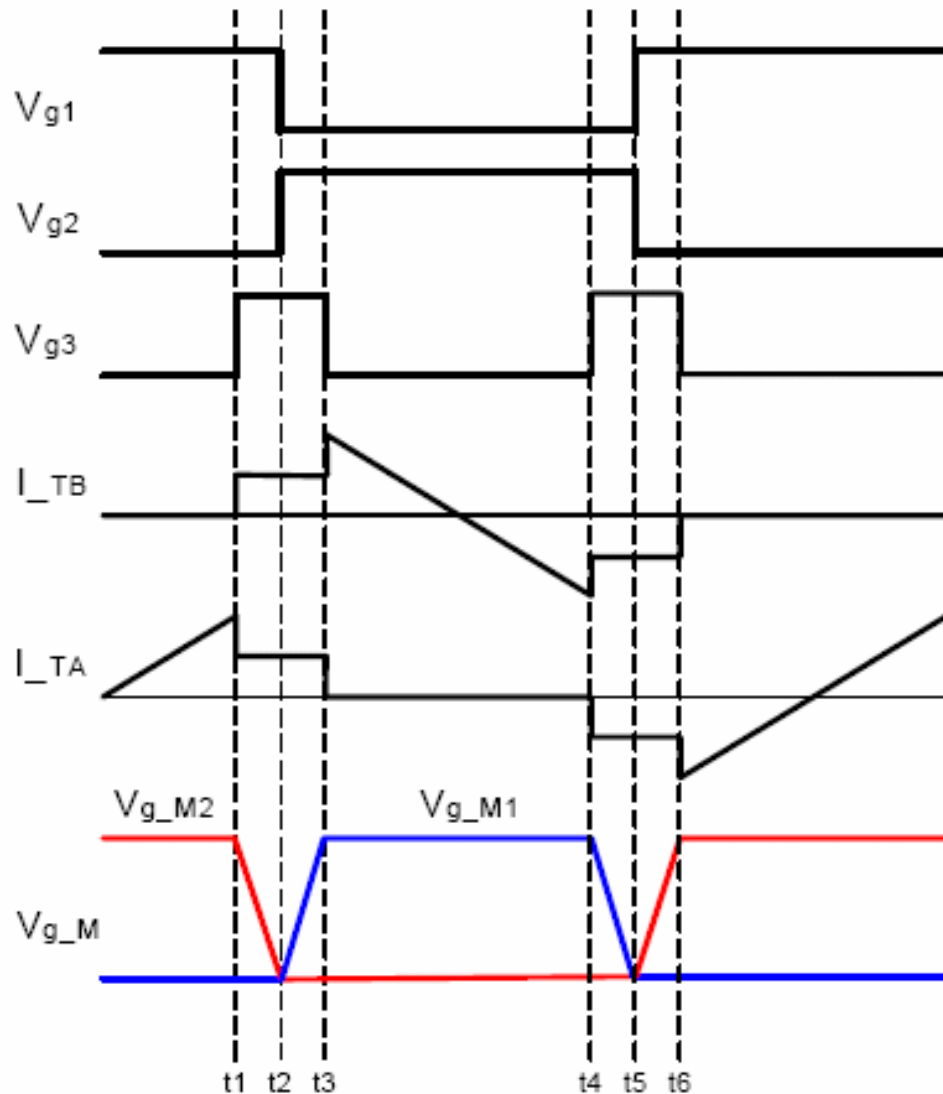
Operating Principles



$t1 \sim t2$:

1. S3 turned off at $t1$
2. Magnetizing current discharges C_g of M2
3. M2 turned off
4. S2 is turned on at ZVS

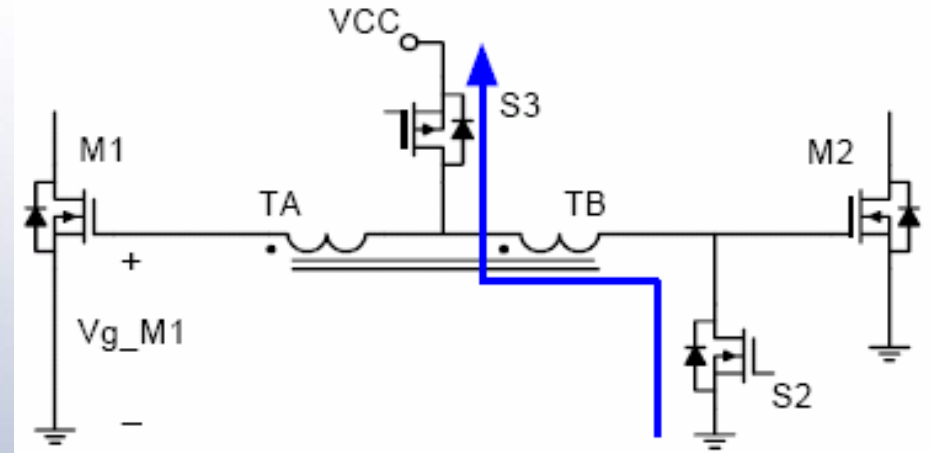
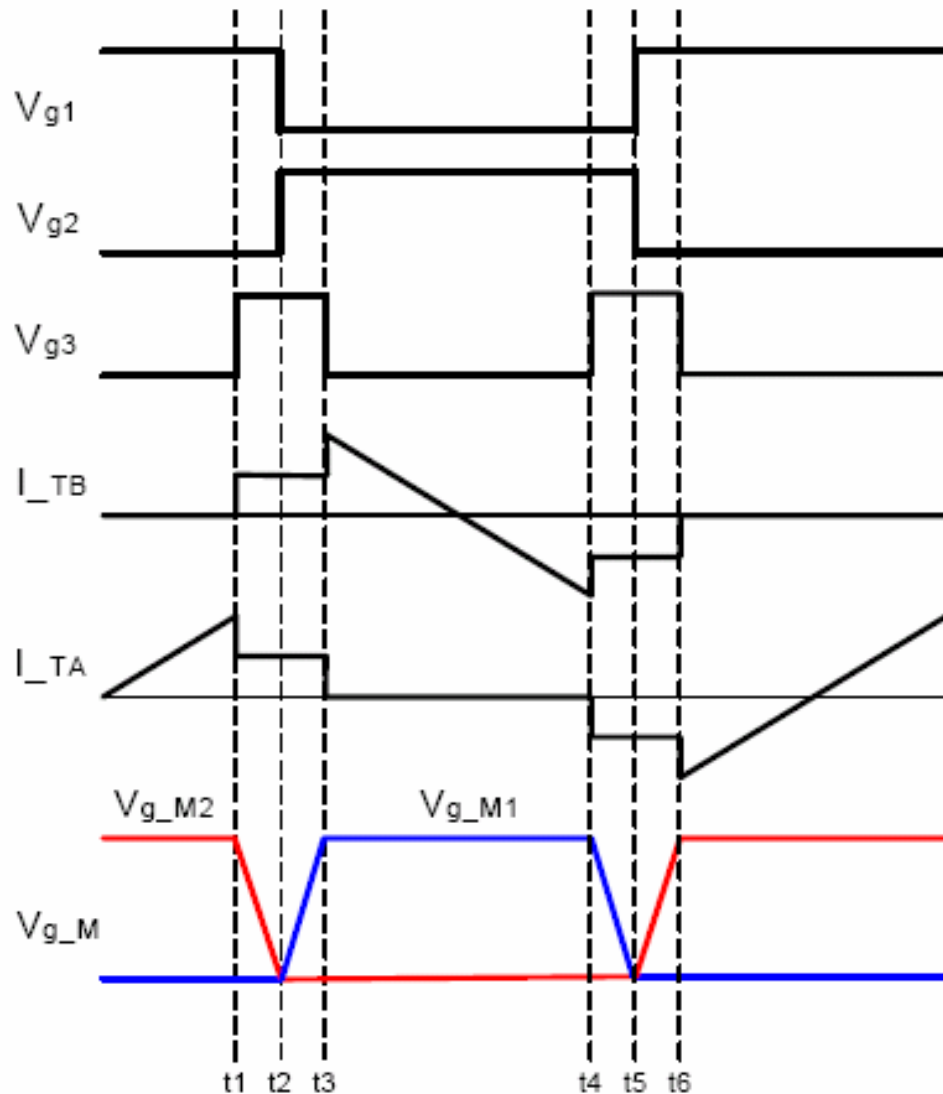
Operating Principles



t2 ~ t3:

1. At t2, S1 turned off
2. Magnetizing current charges C_g of M1
3. V_g of M1 is charged to twice of V_{cc}
4. Body diode of S3 conducts current

Operating Principles



After t_3 :

1. At t_3 , S3 turned on at ZVS
2. M1 on, M2 off
3. Gate voltage of M1 at twice of V_{cc}

Advantages



- **Current source to charge and discharge the gate capacitance**
 - **Switching loss can be reduced!**
- **$V_{gs} = 2V_{cc}$**
 - Conduction loss is reduced
 - Logic level source for V_{cc}
- **Drives a pair of MOSFETs**

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3. Analysis and Design Guidelines



Resonant Gate Driver Loss Components

$$P_{gr} = P_{rms} + P_{drive} + P_{core}$$

1. Conduction loss – main contributor

2. Control switch driving loss – small share

- Select low gate charge control switches while conscious of R_{ds} conduction loss
- **ZVS for control switches**

3. Core loss – small share

Conduction Loss Analysis



Conduction loss calculation:

$$P_{rms} = I_{ss_rms}^2 \cdot (2R_{ds_on} + R_L) + 2 \cdot I_{t_rms}^2 \cdot (R_g + 2R_L + R_{ds_on})$$

$$I_{ss_rms} = \frac{I_{pk}}{\sqrt{3}}$$

$$I_{t_rms} = \frac{I_{pk}}{2} \cdot \sqrt{\frac{T_t}{T_s}}$$

Relationship between driving speed and driving current:

$$I_{pk} = \frac{4 \cdot V_{CC} \cdot C_g}{T_t}$$

Transformer Design



- **Center tapped transformer**
- **Bifilar wire winding construction to minimize leakage inductance impact**

Presentation Overview



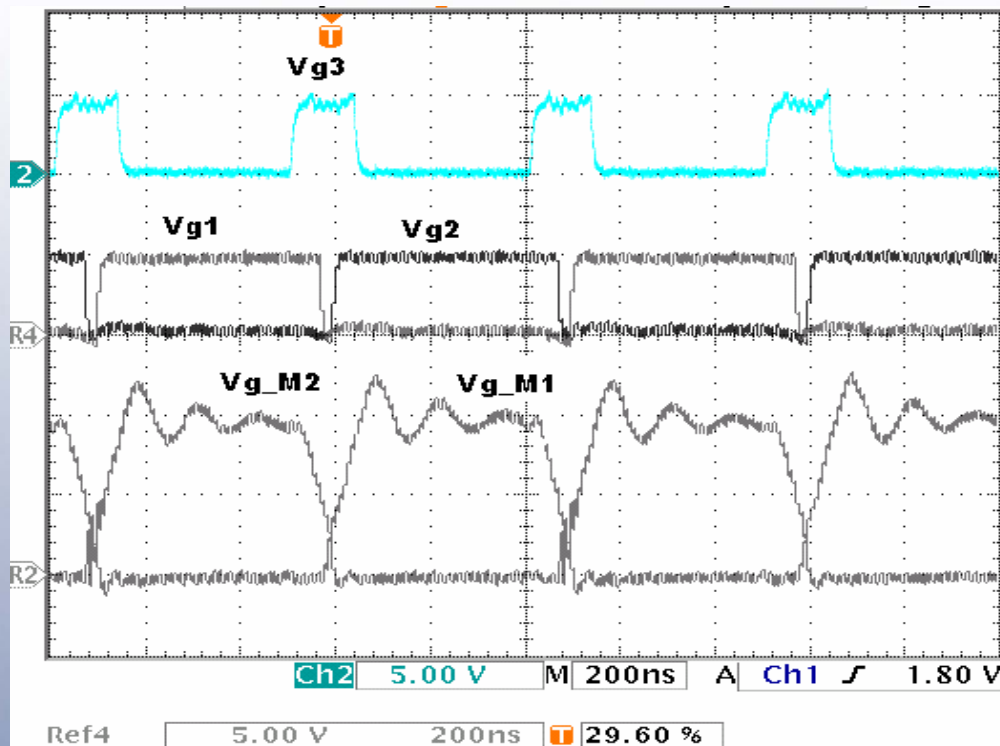
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Experimental Results:

$V_{cc}=5V$, 1MHz, $L_m=900nH$, 2-FDS4410



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Recovery:

- 48% loss saving 2-FDS4410 paralleled
- 64% loss saving $R_g=0.22\Omega$, $C_g=3.9nF$

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5. Conclusions



- **A new resonant gate drive circuit was introduced**
- **Circuit drives a pair of MOSFETs**
- **Driving voltage is twice V_{cc}**
- **Approximately 50% gate energy recovery**